Optical Lithography Processing of AZ 1512 HS

- Clean sample using Acetone & IPA and dry in oven at 85°C for 15 minutes
- Spin AZ1512 at 4000 rpm for 40 s (gives 1.2 µm thick resist layer)
- Pre-bake at 85°C for 15 minutes
- Expose for 10 s (Hard Contact)
- Develop in 1:1 AZ 321 developer for ~ 20s or AZ 721 developer for 20 s (depending on the feature size and gap)
- Footage removal in O_2 plasma (0.9 Torr, 90 sccm, 20 W, 1 minute)